

0.2 GHz to 8 GHz, GaAs, HBT MMIC, Divide by 8 Prescaler

Enhanced Product

HMC434-EP

FEATURES

Ultralow SSB phase noise: –150 dBc/Hz typical Single-ended input/outputs RF output power: –2 dBm typical Single-supply operation: 3 V Ultrasmall, surface-mount, 2.90 mm × 2.80 mm, 6-lead SOT-23 package

ENHANCED PRODUCT FEATURES

Supports defense and aerospace applications (AQEC standard) Extended industrial temperature range: -55°C to +105°C Controlled manufacturing baseline 1 assembly/test site 1 fabrication site Product change notification Qualification data available upon request

APPLICATIONS

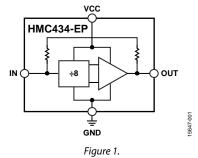
DC to C band PLL prescalers Very small aperture terminal (VSAT) radios Unlicensed national information infrastructure (UNII) and point to point radios IEEE 802.11a and high performance radio local area network (HiperLAN) WLAN Fiber optics Cellular/3G infrastructure

GENERAL DESCRIPTION

The HMC434-EP is a low noise, static, divide by 8 prescaler monolithic microwave integrated circuit (MMIC) utilizing indium gallium phosphide/gallium arsenide (InGaP/GaAs) heterojunction bipolar transistor (HBT) technology in an ultrasmall surface-mount 6-lead SOT-23 package.

The HMC434-EP operates from near dc (square wave) or 0.2 GHz (sine wave) to 8 GHz input frequency with a single 3 V dc supply.

FUNCTIONAL BLOCK DIAGRAM



The HMC434-EP features single-ended inputs and outputs for reduced component count and cost. The low additive single sideband (SSB) phase noise of -150 dBc/Hz at 100 kHz offset helps the user maintain optimal system noise performance.

Additional application and technical information can be found in the HMC434 data sheet.

Rev. B

Document Feedback

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REVISION HISTORY

| 3/2019—Rev. A to Rev. B | |
|-------------------------|---|
| Changes to Figure 11 | 5 |

| 8/2017—Rev. 0 to Rev. A |
|---|
| Changes to Features Section and General Description Section 1 |
| Added Endnote 2 to Table 1 |

3/2017—Revision 0: Initial Version

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SPECIFICATIONS

 V_{CC} = 3 V, T_A = 25°C, 50 Ω system, unless otherwise noted. P_{IN} is input power.

Table 1.

| Parameter | Min | Тур | Max | Unit | Test Conditions / Comments |
|----------------------------|------|------|------|--------|--|
| RADIO FREQUENCY (RF) INPUT | | | | | |
| Frequency ^{1, 2} | 0.2 | | 8 | GHz | Sine wave input |
| Power | -10 | 0 | +10 | dBm | $f_{IN} = 1.0 \text{ GHz}$ to 3.0 GHz |
| | 0 | 0 | 10 | dBm | $f_{IN} = 3.0 \text{ GHz}$ to 8.0 GHz |
| RF OUTPUT | | | | | |
| SSB Phase Noise | | -150 | | dBc/Hz | 100 kHz offset, $P_{IN} = 0 \text{ dBm}$, $f_{IN} = 4.0 \text{ GHz}$ |
| Power | -5 | -2 | | dBm | $f_{IN} = 1.0 \text{ GHz}$ to 8.0 GHz |
| REVERSE LEAKAGE | | -25 | | dBm | $P_{IN} = 0 \text{ dBm}, f_{IN} = 4.0 \text{ GHz}$, output terminated |
| SUPPLY | | | | | |
| Voltage (V _{cc}) | 2.85 | 3 | 3.15 | V | |
| Current (Icc) | | 62 | 83 | mA | |

¹ Below 200 MHz, a square wave input is required. ² For stable operation without an input signal, refer to the AN-1463 Application Note, Frequency Divider Operation and Compensation with No Input Signal.

ABSOLUTE MAXIMUM RATINGS

Table 2.

| Parameter | Rating | | | |
|--|------------------|--|--|--|
| Supply Voltage (V _{CC}) | –0.3 V to +3.5 V | | | |
| RF Input Power (V _{CC} = 3 V) | 13 dBm | | | |
| Temperature | | | | |
| Operating | -55°C to +105°C | | | |
| Storage | –65°C to +125°C | | | |
| Junction, T _J | 135°C | | | |
| Nominal ($T_A = 105^{\circ}C$) | 119°C | | | |
| Reflow | 260°C | | | |
| ESD Sensitivity | | | | |
| Human Body Model (HBM) | Class 0 | | | |

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

THERMAL RESISTANCE

Thermal performance is directly linked to printed circuit board (PCB) design and operating environment. Careful attention to PCB thermal design is required.

 θ_{JA} is the natural convection junction to ambient thermal resistance measured in a one cubic foot sealed enclosure. θ_{JC} is the junction to case thermal resistance.

Table 3. Thermal Resistance

| Package Type | θ_{JA}^{1} | θ _{JC} ² | Unit |
|--------------|-------------------|------------------------------|------|
| RJ-6 | 359 | 70 | °C/W |

¹ Simulated values per JEDEC JESD51-12 standards.

² Junction to GND package pin.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

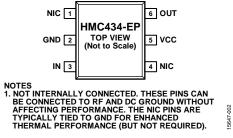


Figure 2. Pin Configuration

Table 4. Pin Function Descriptions

| Pin No. | Mnemonic | Description |
|---------|----------|---|
| 1, 4 | NIC | Not Internally Connected. These pins can be connected to RF and dc ground without affecting performance. The NIC pins are typically tied to GND for enhanced thermal performance (but not required). |
| 2 | GND | Ground. This pin must be connected to both RF and dc ground. |
| 3 | IN | RF Input. This pin must be dc blocked. |
| 5 | VCC | Supply Voltage (3 V). |
| 6 | OUT | RF Output. This pin must be dc blocked. |

INTERFACE SCHEMATICS



Figure 3. GND Interface Schematic

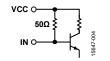


Figure 4. IN Interface Schematic

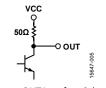


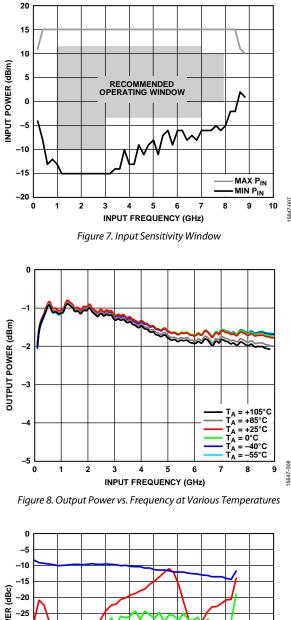
Figure 5. OUT Interface Schematic



Figure 6. VCC Interface Schematic

TYPICAL PERFORMANCE CHARACTERISTICS

In Figure 9, PFEEDTHROUGH is the power of the output spectrum at the input frequency.



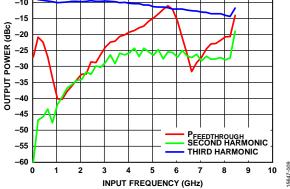
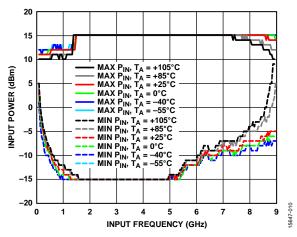
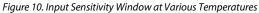
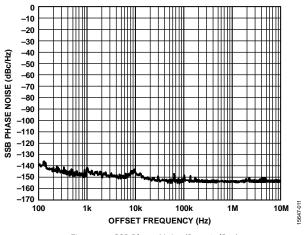


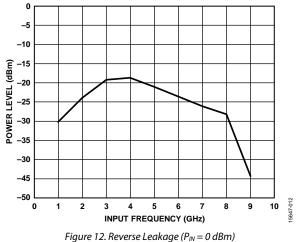
Figure 9. Output Harmonic Content ($P_{IN} = 0 dBm$)



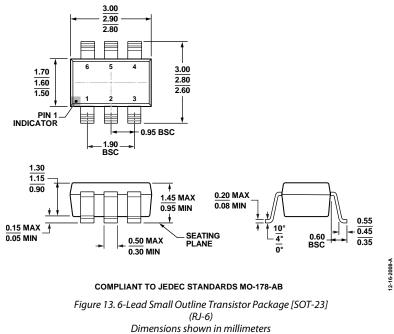








OUTLINE DIMENSIONS



ORDERING GUIDE

| Model ¹ | Temperature Range | Package Description | Package Option | Marking Code |
|--------------------|-------------------|--|----------------|--------------|
| HMC434SRJZ-EP-PT | –55°C to +105°C | 6-Lead Small Outline Transistor Package [SOT-23] | RJ-6 | 34P |
| HMC434SRJZ-EP-R7 | –55°C to +105°C | 6-Lead Small Outline Transistor Package [SOT-23] | RJ-6 | 34P |

 1 Z = RoHs Compliant Part.

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